

Claim 1 (Amended):

Sub B1
A process for the wet chemical treatment of semiconductor wafers with treatment liquids in baths, comprising the steps of

firstly treating the semiconductor wafers in a bath with an aqueous HF solution;

A1
then treating the semiconductor wafers in a bath with an aqueous O₃ solution; and

then treating the semiconductor wafers in a bath with [a liquid selected from the group consisting of water and] an aqueous HCl solution;

[whereby] wherein these treatment steps [forming] form a treatment sequence B₂ which does not need to be interrupted by rinsing with water or another treatment liquid.

In claim 2, in line 3

after "aqueous" please cancel "SC1" and insert --SC-1--.

In claim 9, in line 2

after "aqueous" please cancel "SC1" and insert --SC-1--.

Please add new claim 11.

11. A process for the wet chemical treatment of semiconductor wafers with treatment liquids in baths, comprising the steps of

Sub 11.2
firstly treating the semiconductor wafers in a bath with an aqueous HF solution;

then treating the semiconductor wafers in a bath with an aqueous O₃ solution; and

A 8
then treating the semiconductor wafers in a bath with an aqueous HCl solution with exposure to megasonic waves,

whereby these treatment steps form a treatment sequence B₂, which avoids the addition of fresh water or other liquids to the treatment baths.

REMARKS

Reconsideration of this patent application is respectfully requested in view of the foregoing amendments, and the following remarks.